

TECHNICAL DATA  
DATA SHEET 200, REV D

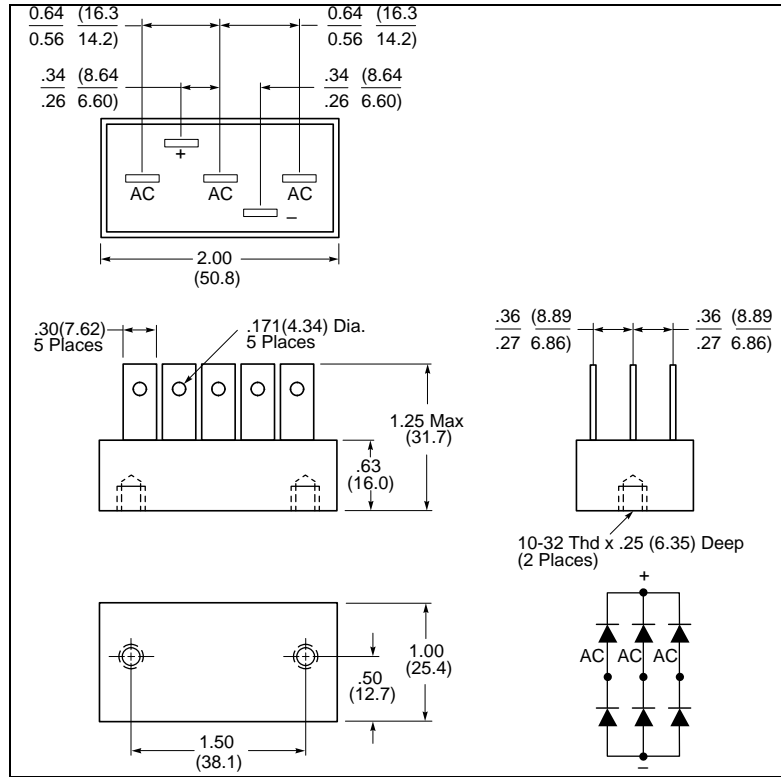
## THREE PHASE FULL WAVE BRIDGE RECTIFIER ASSEMBLY

DESCRIPTION: 600 VOLT, 50 AMP, 195 NANOSECOND THREE PHASE BRIDGE RECTIFIER ASSEMBLY.

MAX. RATINGS / ELECTRICAL CHARACTERISTICS All ratings are at  $T_A = 25^\circ\text{C}$  unless otherwise specified.

RATING	CONDITIONS	MIN	MAX	UNIT
Peak Inverse Voltage (PIV)	S50A360FR S50A340FR	-	600 400	Vdc
Average DC Output Current ( $T_C = \text{Case Temp}$ ) ( $I_o$ )	$T_C = 55^\circ\text{C}$ $T_C = 100^\circ\text{C}$ $T_C = 125^\circ\text{C}$	-	50 33 25	Amps
Average DC Output Current Ambient Temp. (no heat sink) ( $I_o$ )	$T_A = 25^\circ\text{C}$ $T_A = 55^\circ\text{C}$ $T_A = 100^\circ\text{C}$	-	12.5 10 6.0	Amps
Peak Single Cycle Surge Current ( $I_{FSM}$ )	$t_p = 8.3$ ms Single Half Cycle Sine Wave, Superimposed On Rated Load	-	240	Amps(pk)
Peak Recurring Surge Current ( $I_{FRM}$ )	$T_A = 25^\circ\text{C}$	-	150	Amps
Operating and Storage Temp. ( $T_{op}$ & $T_{stg}$ )	-	-55	+150	$^\circ\text{C}$
Maximum Forward Voltage ( $V_f$ )	$I_f = 10\text{A}$ (300 $\mu\text{sec}$ pulse, duty cycle < 2%)	-	1.2	Volts
Maximum Instantaneous Reverse Current At Rated (PIV)	$T_A = 25^\circ\text{C}$ $T_A = 100^\circ\text{C}$	-	9.0 180	$\mu\text{Amps}$
Reverse Recovery Time ( $t_{rr}$ )	$I_f = 0.5\text{A}$ , $I_r = 1.0\text{A}$ , $I_{rr} = 0.25\text{A}$	-	195	nsec
Thermal Resistance ( $\theta_{JL}$ )	-	-	0.9	$^\circ\text{C/W}$

**MECHANICAL DIMENSIONS: In inches / mm**



Note: Case finish - Black Anodized

**Fig. 412**

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